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METHOD FOR FORMING CARBONACEOUS
COATING FILM ON CARBON SUBSTRATE

Abstract

PURPOSE: To obtain an uniform, dense and high purity carbonaceous coating film by bringing a silicon carbide covering layer formed on the carbon substrate by CVD method into contact with a prescribed high temp. halogen gas to desiliconize and convert the silicon carbide covering layer to carbonaceous.

CONSTITUTION: An amorphous or polycrystalline uniform and dense structure is formed by depositing the silicon carbide covering layer on the carbon substrate by CVD method. The silicon carbide covering layer is brought into contact with halogen gas at $\geq 1500^{\circ}\text{C}$ to desiliconize and is completely converted to carbonaceous. As a result, the uniform, dense and high purity carbonaceous coating film is obtained.

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